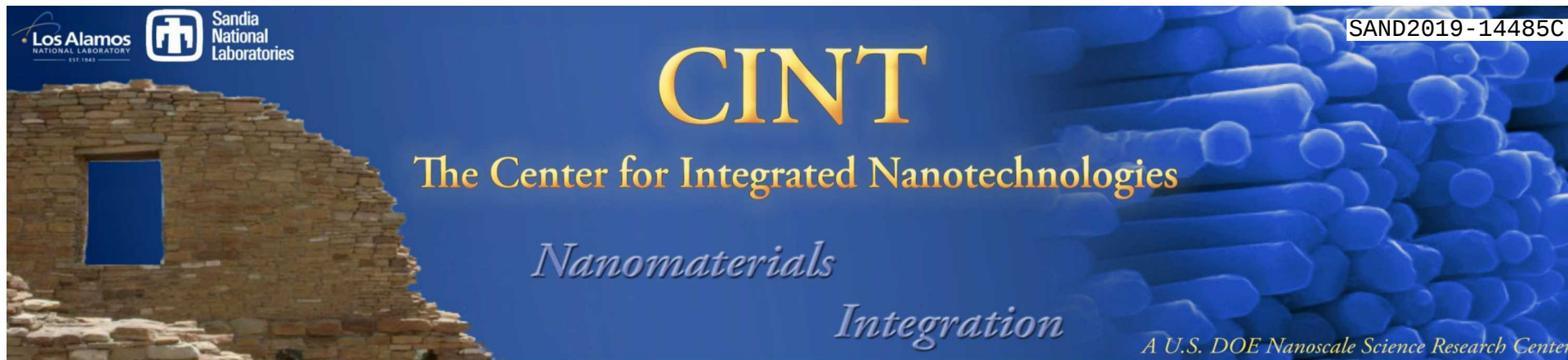




Experimental Determination of the Ionization Energies of MoSe_2 , WS_2 , and MoS_2 Using Photoemission Electron Microscopy

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LEEM-PEEM contact: Taisuke Ohta, tohta@sandia.gov

December 2, 2019

MQ03.02.06 MRS Fall Meeting

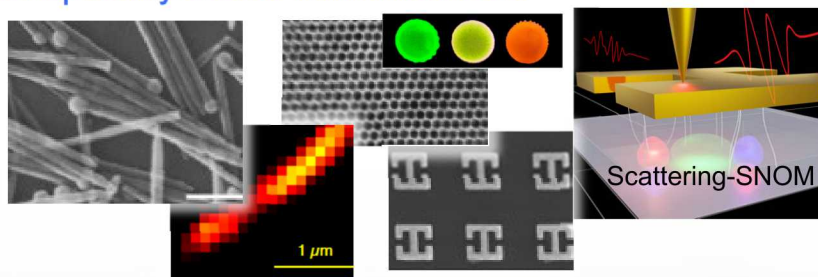
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CINT is a DOE user facility with focuses on Nano Science & Nano Integration

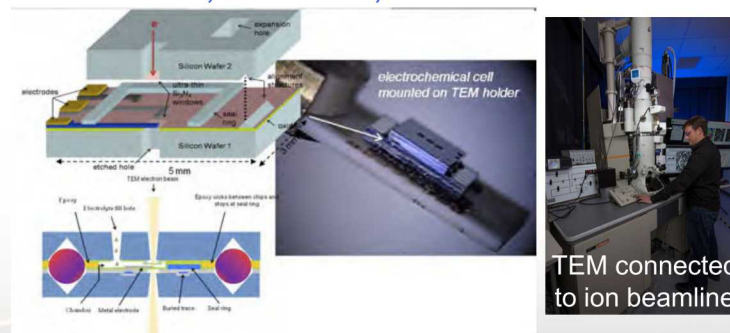
Nanophotonics & Optical Nanomaterials (NPON)

Synthesis, excitation, and energy transformations of optically active nanomaterials



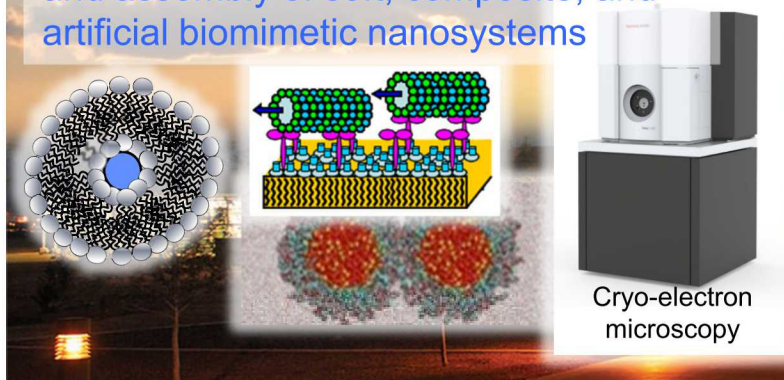
In-situ Characterization and Nanomechanics

Developing capabilities to study the dynamic response of materials and nanosystems to mechanical, electrical, or other stimuli



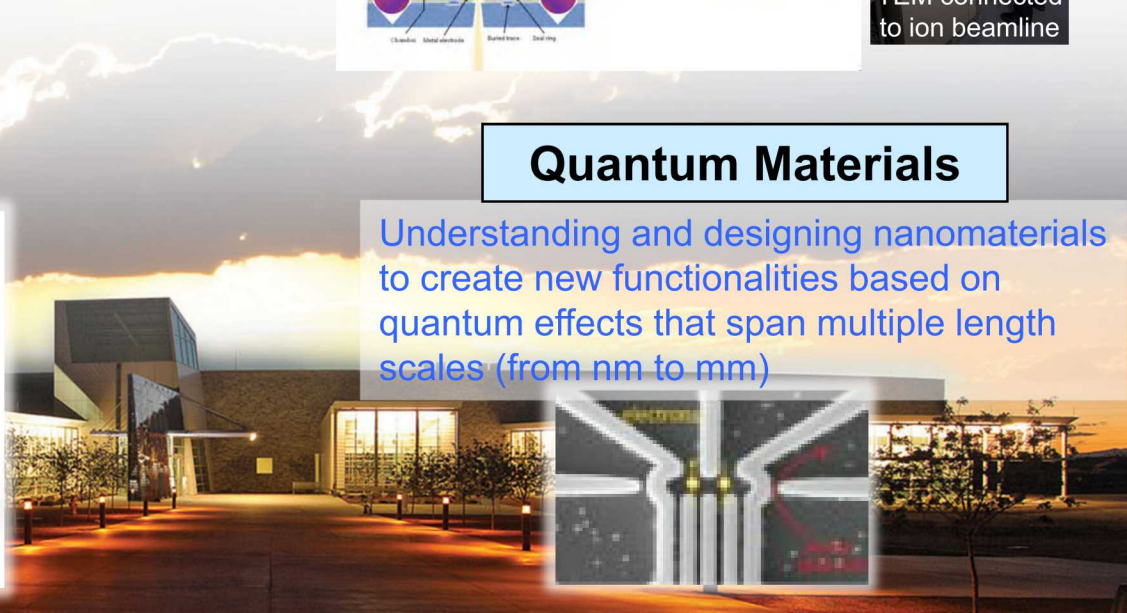
Soft, Biological, & Composite Nanomaterials (SBCN)

Solution-based nanomaterials synthesis and assembly of soft, composite, and artificial biomimetic nanosystems

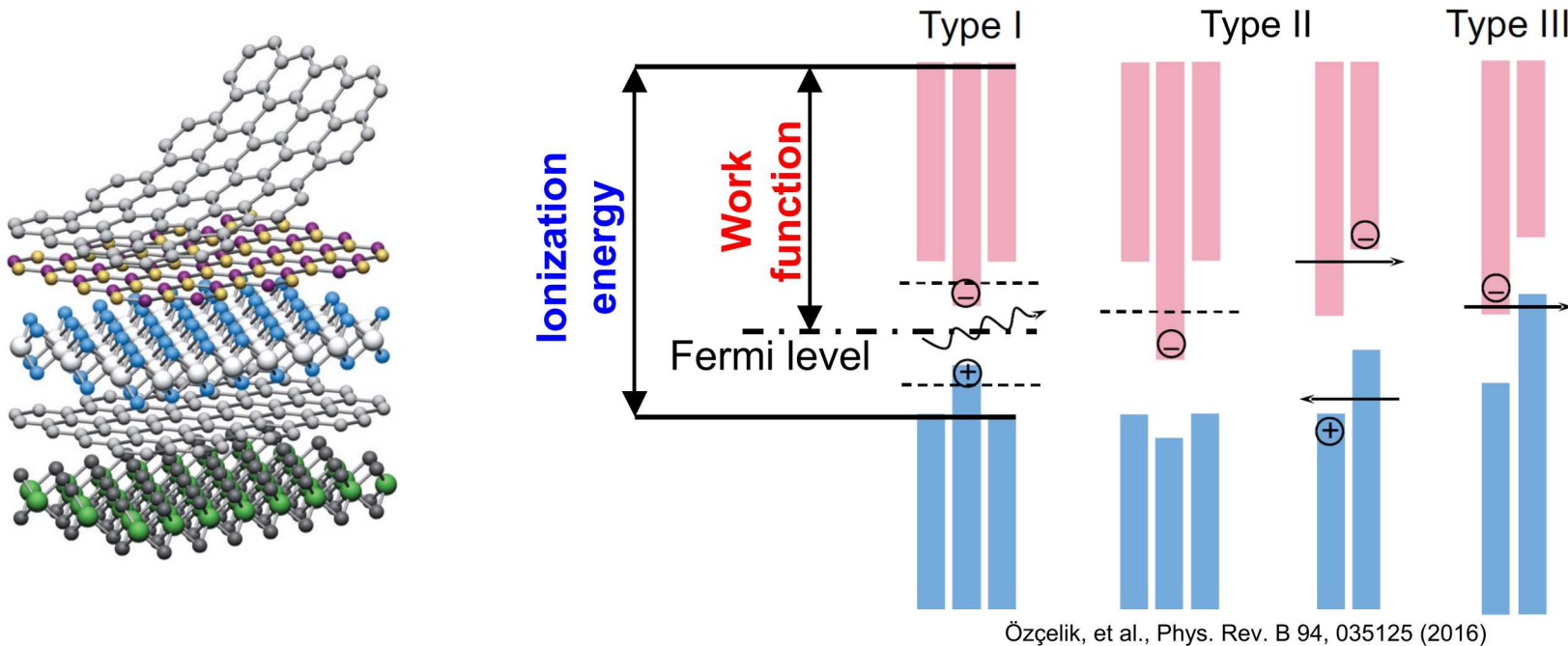


Quantum Materials

Understanding and designing nanomaterials to create new functionalities based on quantum effects that span multiple length scales (from nm to mm)



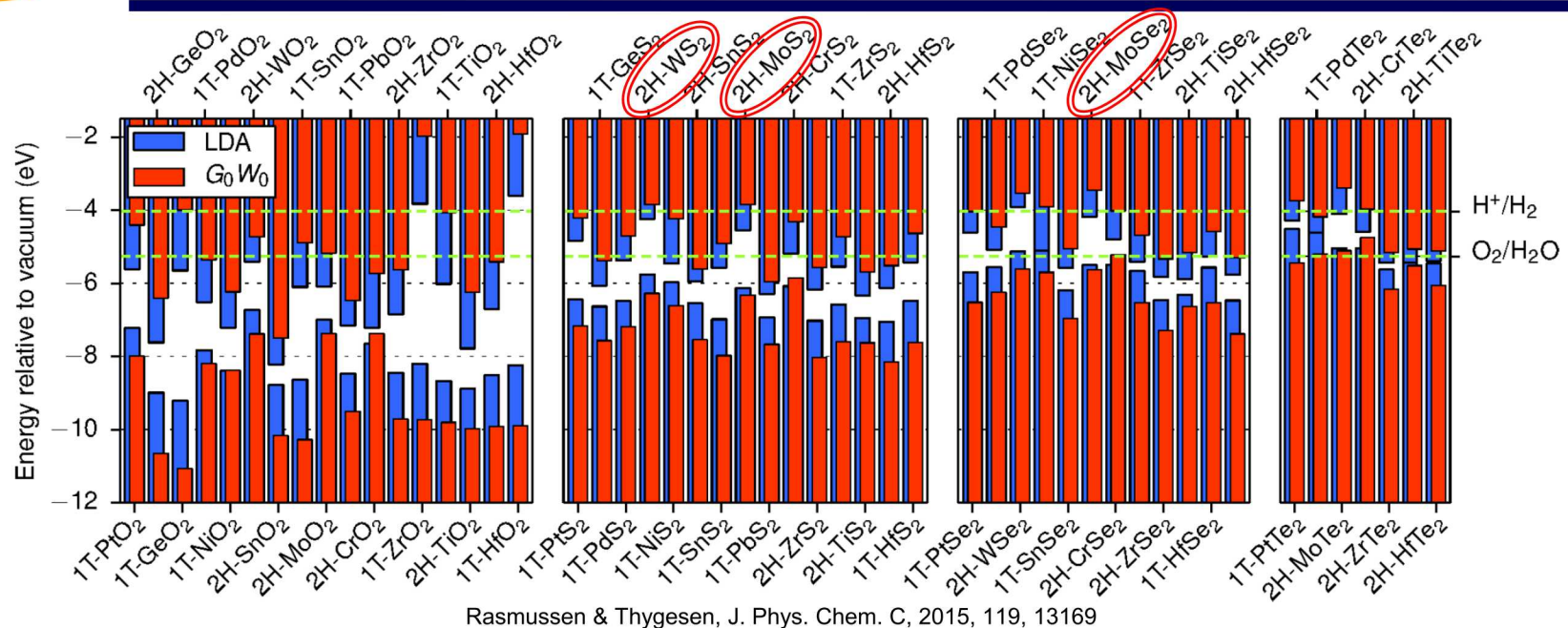
Band alignment of transition metal dichalcogenide dictates the properties of TMD heterostructures



TMDs are ideal platforms to create heterostructures with designed properties



Most studies of the ionization energies are based on modeling

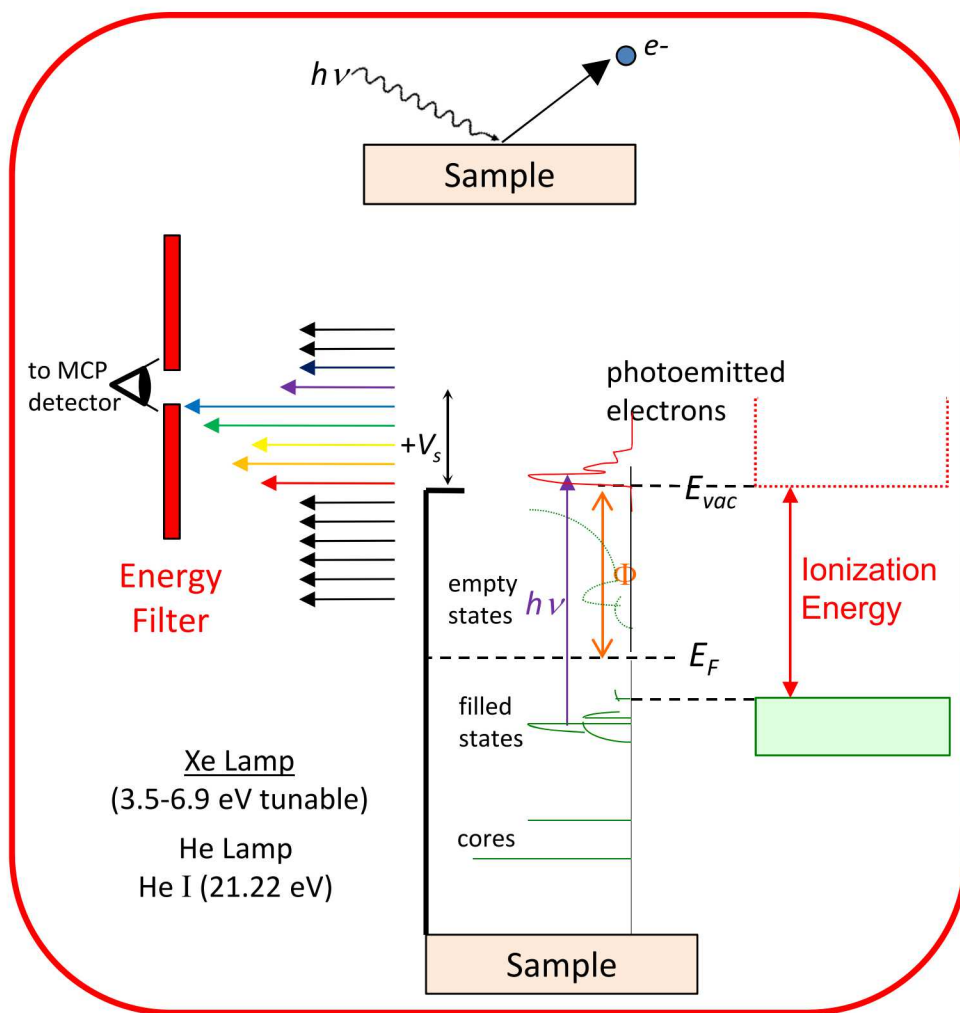


Systematic experimental verification is missing

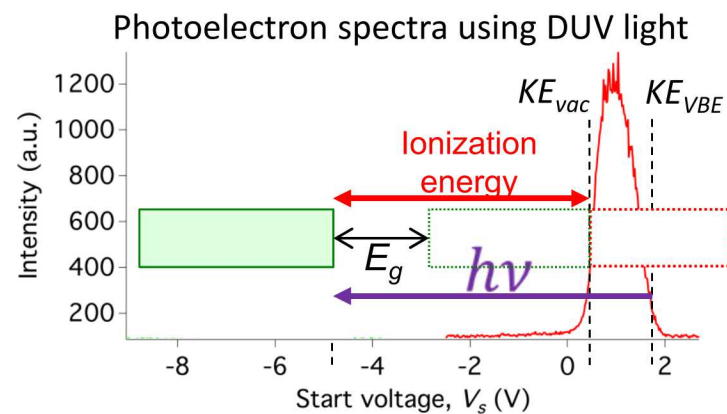
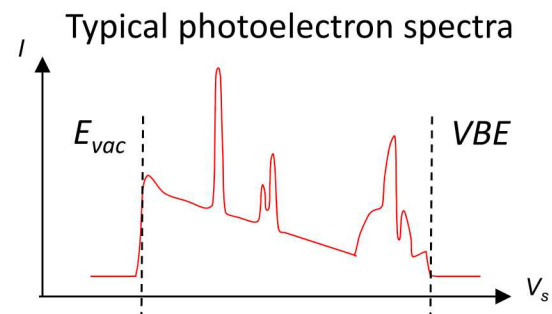
Required (or preferred) characteristics for the experimental approach

- Microscopy function to locate small specimens (good lateral resolution)
- Environment that has little impact on the sample's electronic properties, i.e. vacuum
- Adequate energy resolution
- No need to add a measurement-specific modification to the sample, i.e. electrical ground

We extract E_{vac} & valence band edge at Brillouin zone center from photoelectron (or photoemission) spectra



Photoemission process



$$BE = KE - h\nu$$



We use photoemission microscopy & spectroscopy to evaluate the band alignment

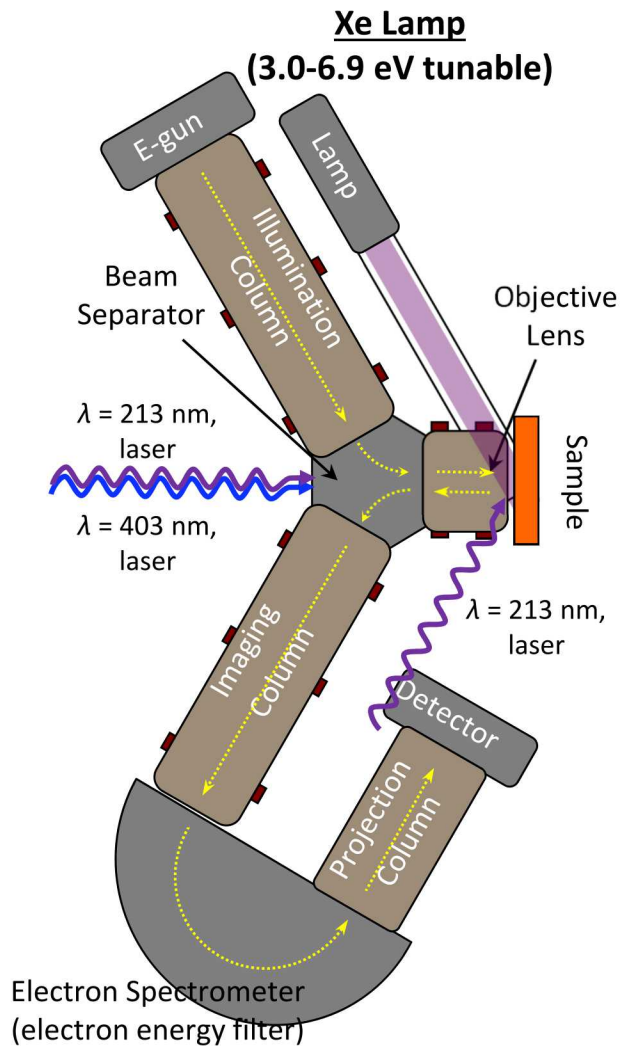


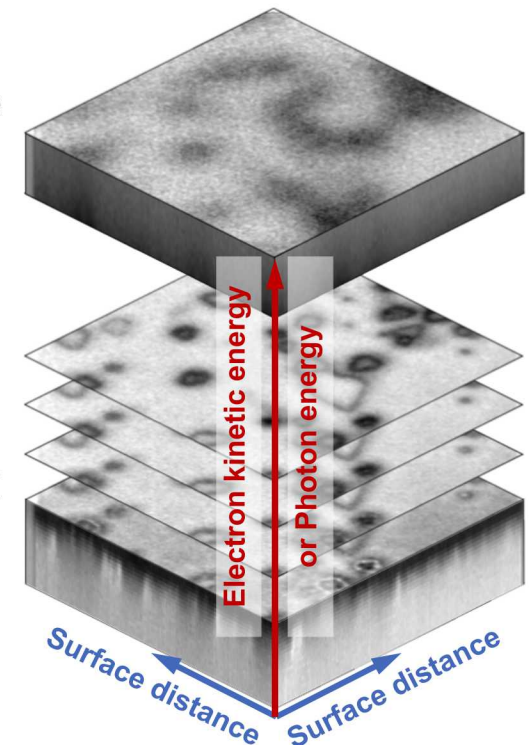
Figure courtesy: M. Berg

- Specifications of the photoemission electron microscope (PEEM)
 - Spatial resolution $\sim 15 - 200\text{nm}$
 - Energy resolution $\sim 0.2 - 0.5\text{eV}$

- Deep UV monochromatic light sources are used for the work presented here
 - $\lambda = 180 - 350\text{nm}$ ($h\nu = 3.54 - 6.89\text{eV}$): tunable-energy photon source based on a Xe-lamp

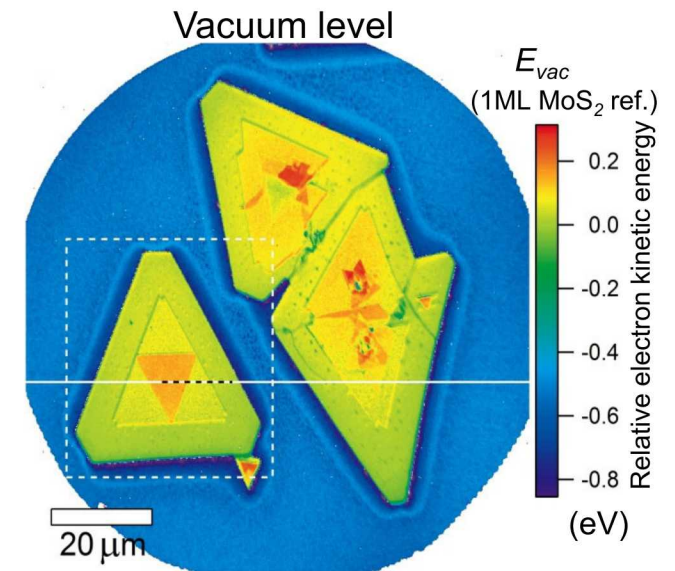
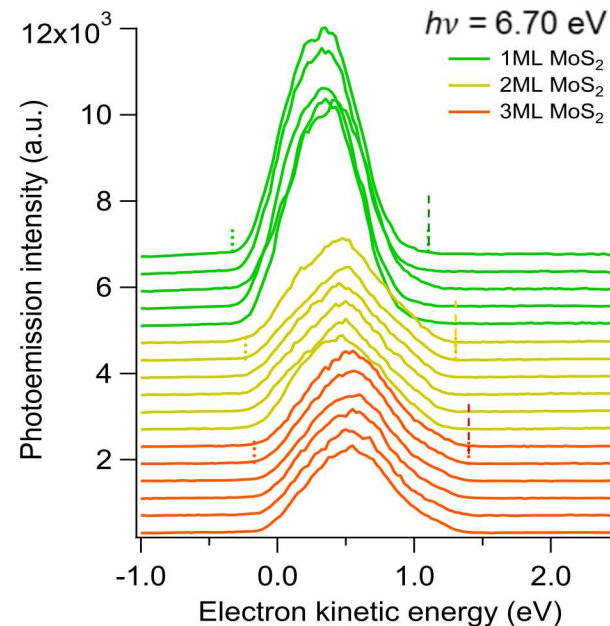
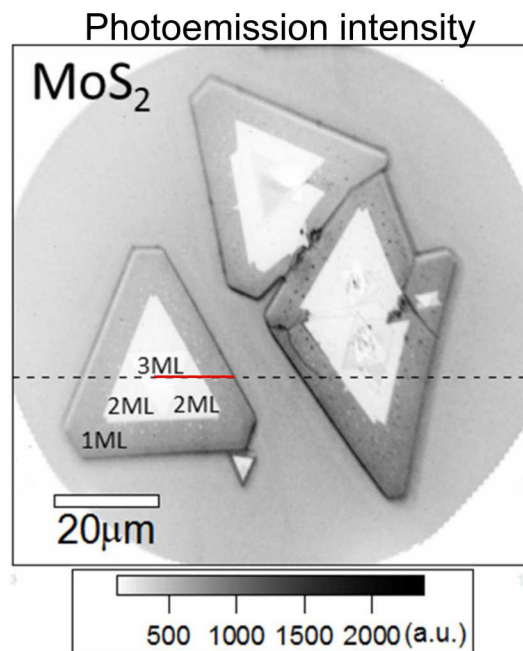
- Spectrum is extracted from each pixel in the image stack or data cube, and fitted to create maps

- Meet the four required (or preferred) characteristics for systematic measurements

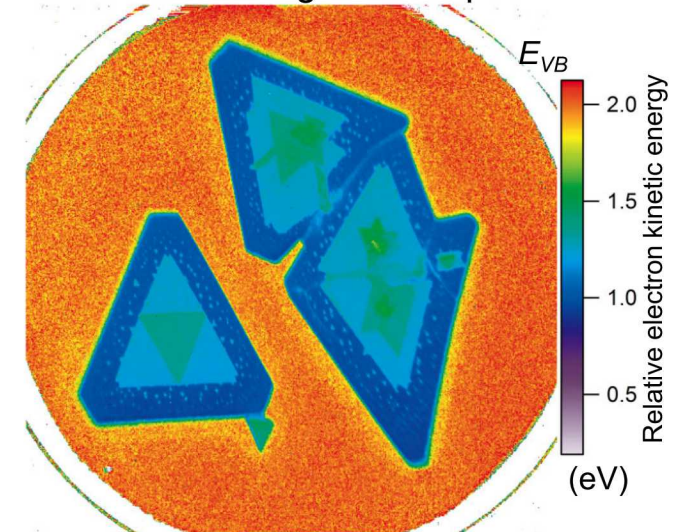




We determine E_{vac} & valence band edge on MoS_2 multi layers



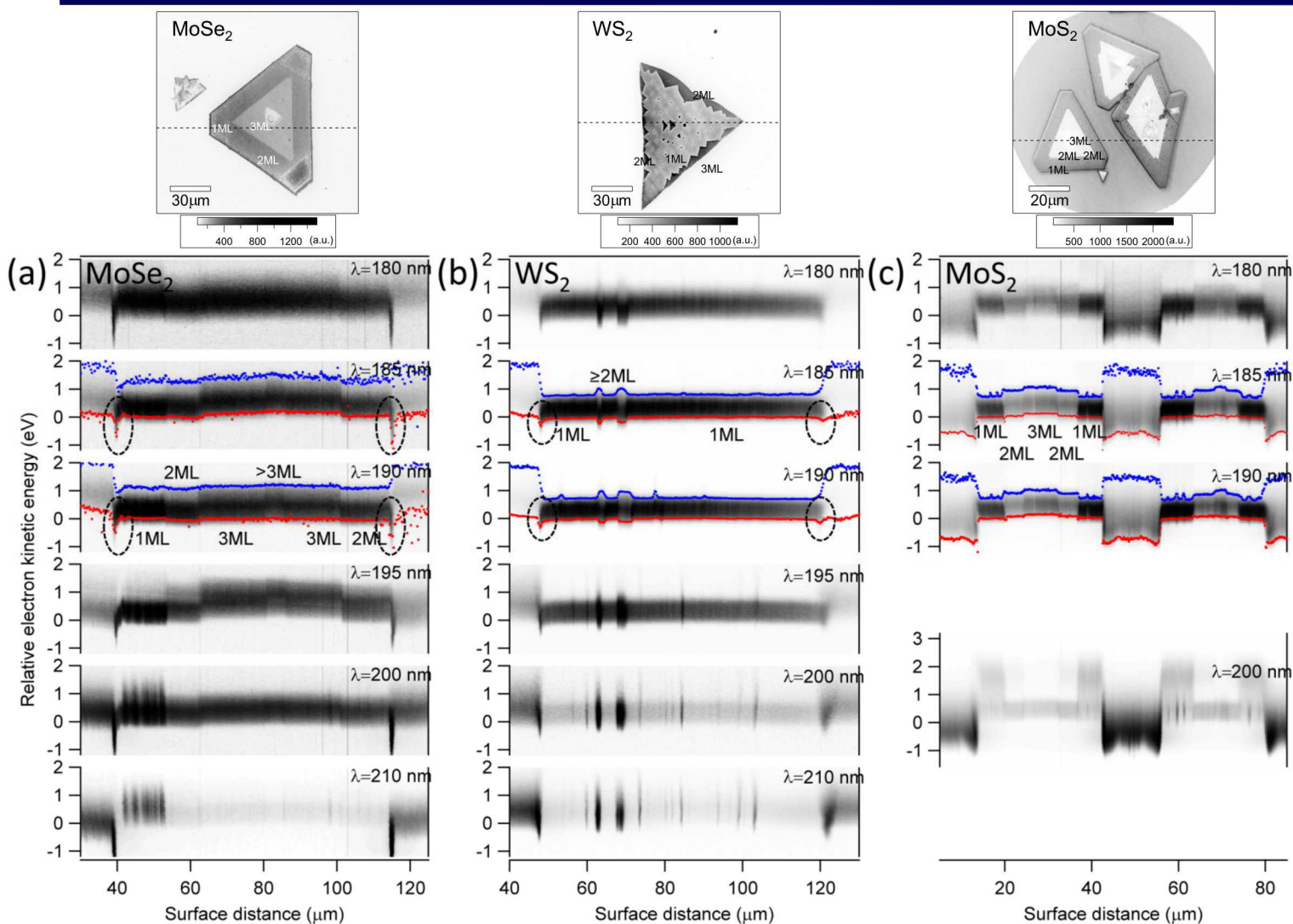
Valence band edge near Γ -point



- Concurrent imaging and spectroscopy



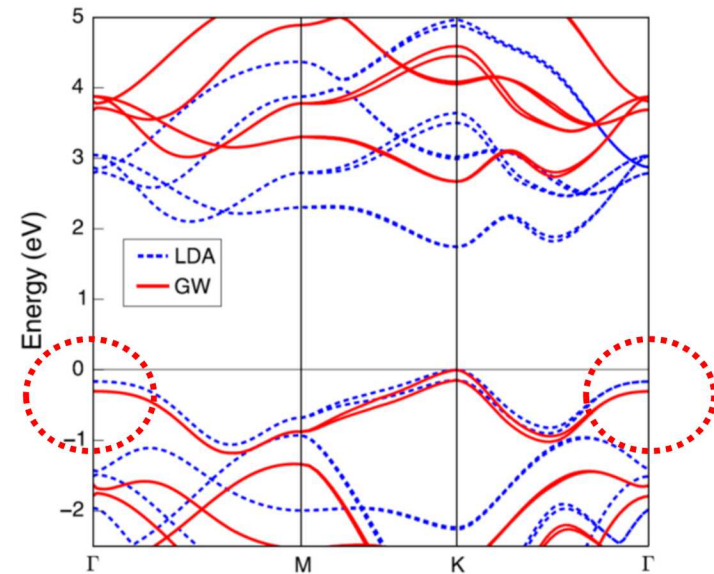
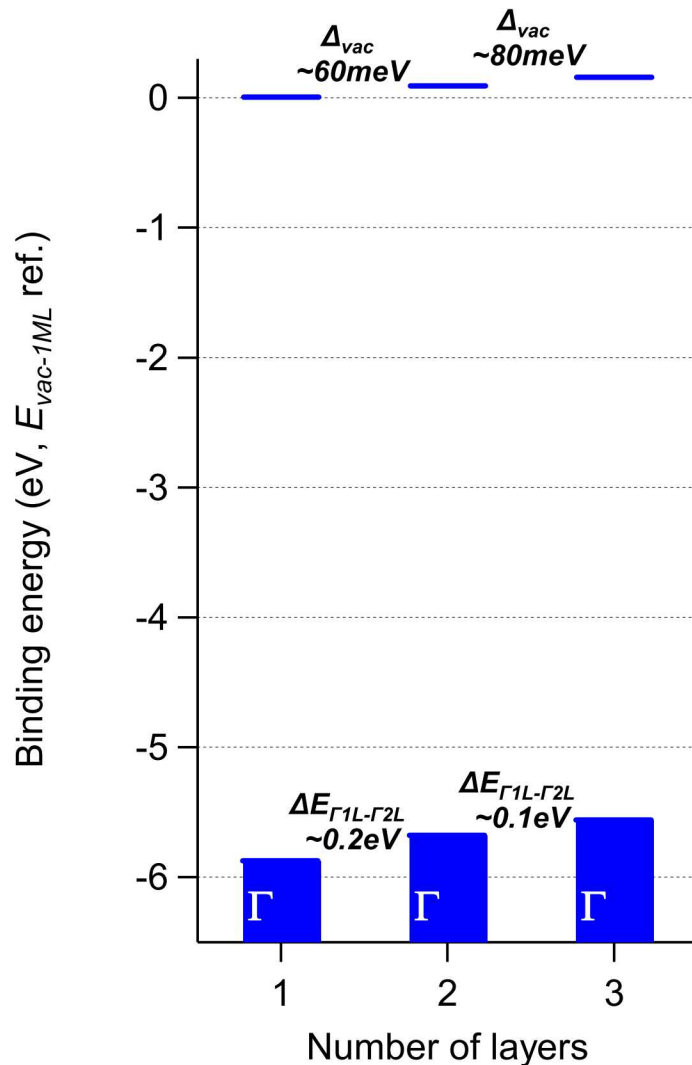
We measure photoemission spectra from MoSe_2 , WS_2 , and MoS_2



K. Keyshar, et al., Experimental determination of the ionization energies of MoS_2 , WS_2 , and MoSe_2 on SiO_2 using photoemission electron microscopy, ACS Nano, 11, 8223, 2017



Hetero-junctions are formed between MoS₂ with different thicknesses



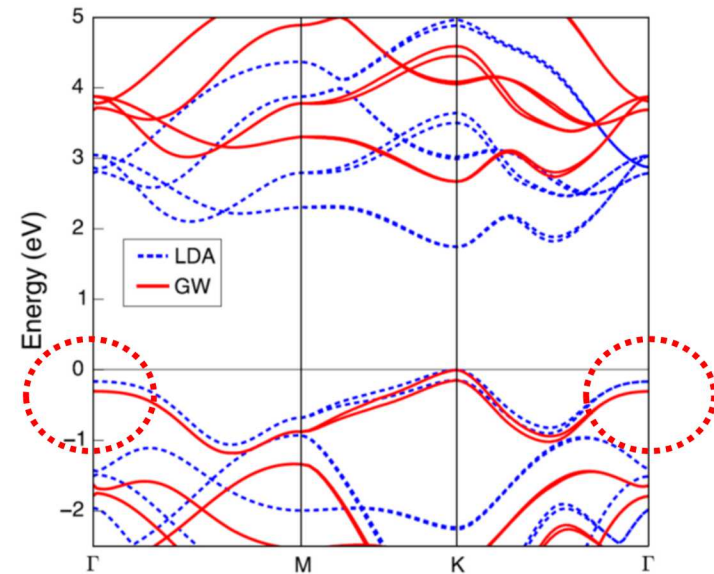
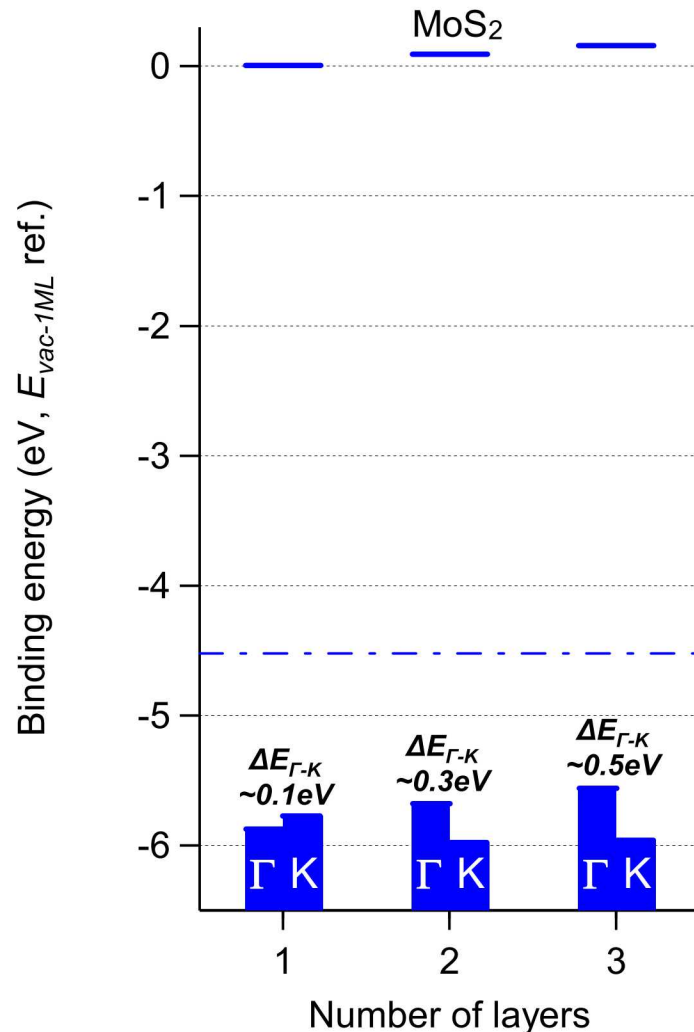
Qiu, et al., Phys. Rev. B 93, 235435 (2016)

- Valence band edge signal comes from near Γ -point due to the limited momentum range accessible by DUV photon-photoemission
- $\Delta E_{\Gamma-K}$ based on DFT calculation

Berg, et al., Layer-Dependence of the Electronic Band Alignment of Few-Layer MoS₂ on SiO₂ Measured Using Photoemission Electron Microscopy, Phys. Rev. B, 95, 235406 (2017)



Hetero-junctions are formed between MoS₂ with different thicknesses



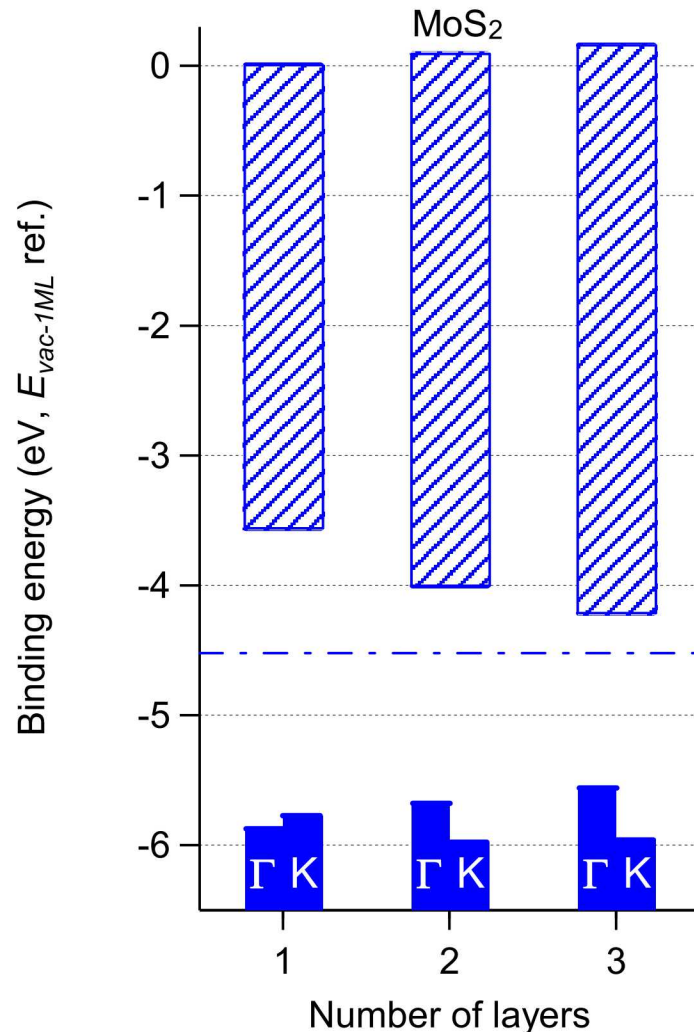
Qiu, et al., Phys. Rev. B 93, 235435 (2016)

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MoS₂ with different thicknesses forms type-I hetero-junctions

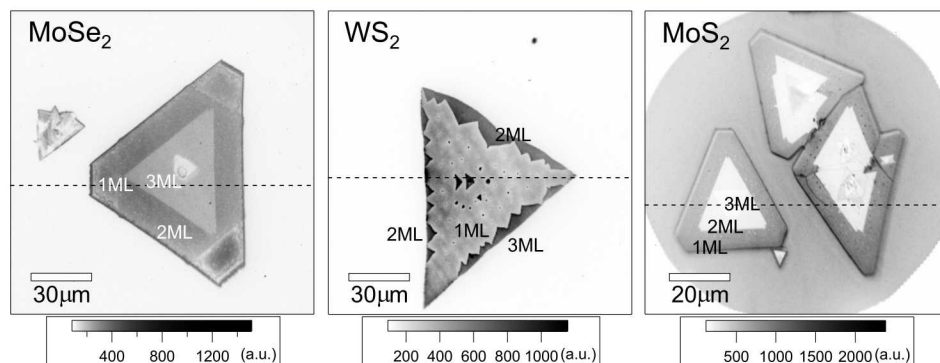


- Experimentally-determined quasi-particle band gap for 1L
 - Liu, et al., PRL, 122, 246803, 2019
 - Rigosi et al., PRB 94, 075440, 2016
- GW-calculated quasi-particle band gap for multilayers
 - Scaled to account for substrate's dielectric environment
- Type-I band alignments at the junctions between monolayer and bilayer and bilayer and trilayer

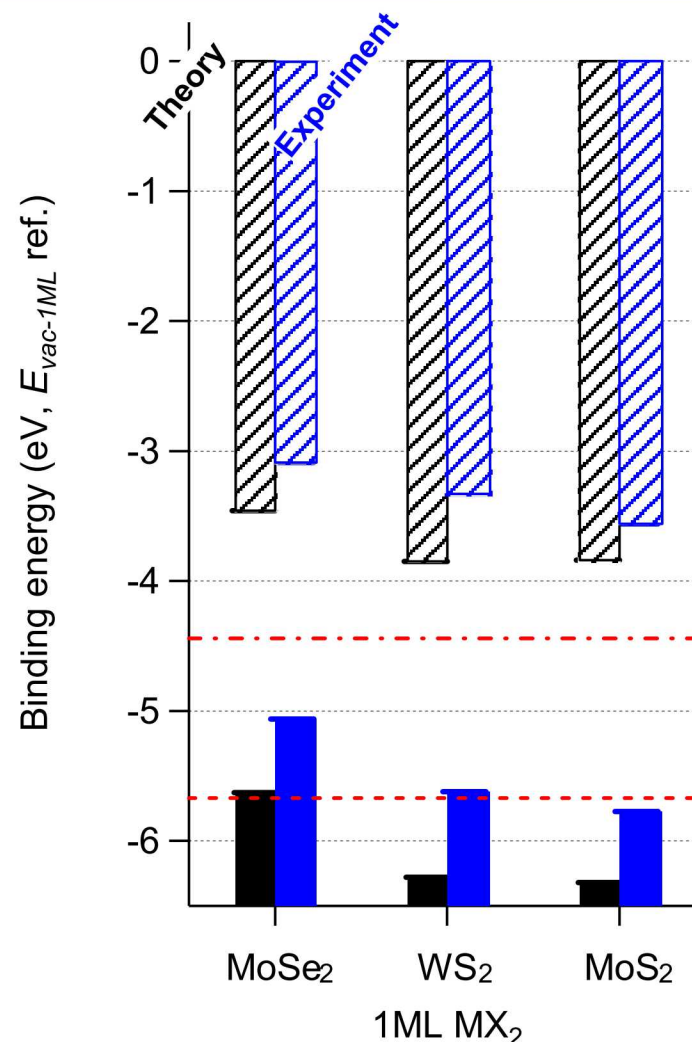
Berg, et al., Layer-Dependence of the Electronic Band Alignment of Few-Layer MoS₂ on SiO₂ Measured Using Photoemission Electron Microscopy, Phys. Rev. B, 95, 235406 (2017)



Experimentally determined ionization energies match well with those from DFT calculations



- Ionization energy decreases from MoS_2 , WS_2 , to MoSe_2 , anticipated from the electronegativities of the constituent atoms
- Good agreement with GW calculation
- Heterostructures containing MoS_2 , WS_2 , to MoSe_2 are likely to display type II alignment

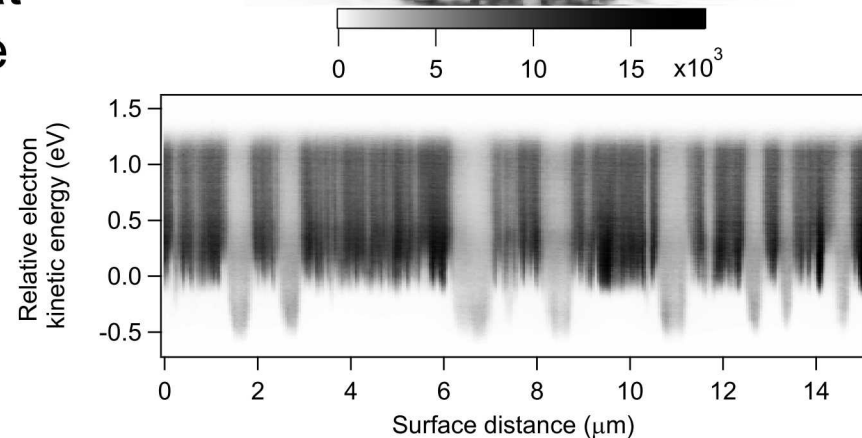
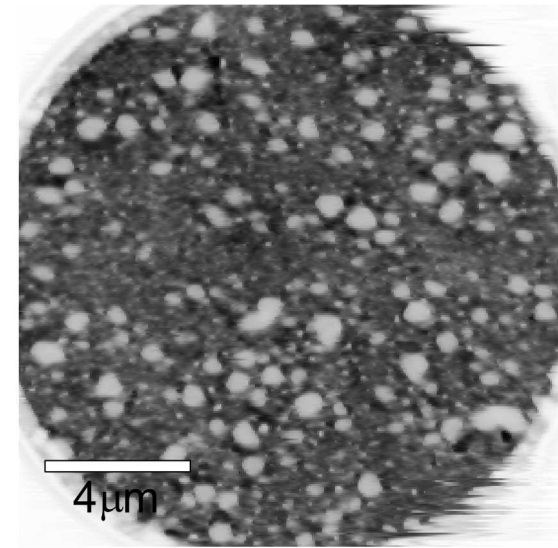




We compare the electronic structures of free-standing and Au-supported WS_2



- Work function of the Au-supported areas is significantly larger than that of free-standing areas reflecting the higher work function of Au



In collaboration with J. Fonseca, J. T. Robinson, Naval Research Laboratory

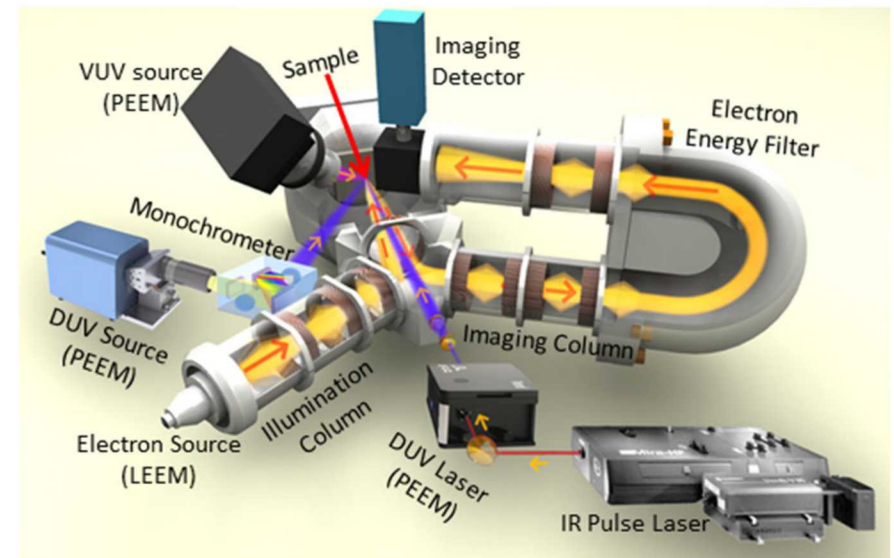
10:15 AM - FF01.08.01, Jose Fonseca, et al., Non-Local Quantum Emission in 2D Semiconductors via Oriented Pore Enabled Network (OPEN) Films



Summary

- PEEM coupled to deep ultraviolet (DUV) light sources is an emerging analytical capability to explore the electronic properties of spatially inhomogeneous materials

- We determined ionization energies of atomically-thin transition metal dichalcogenides and deduced their anticipated heterointerface band alignments



- Other examples:

- Graphene multilayers: Robinson, et al., Scientific Reports 8, 2006 (2018)
- Polycrystalline CdTe: Berg, et al., ACS Appl. Mater. Interfaces, 10, 9817 (2018)
- Polycrystalline metal films: Berg, Bussmann, et al., in preparation

Acknowledgements

- TMDs: Kunttal Keyshar
 - Mohite group, Los Alamos National Lab.
 - Ajayan group, Rice Univ.
 - Berg, Beechem, Chan, Sandia National Labs.
- CdTe: Morgann Berg
 - Berg & Chan, Sandia National Labs.
 - Kephart & Sampath, Colorado State Univ.
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 - Sandia LDRD

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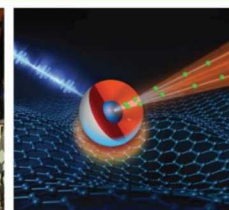
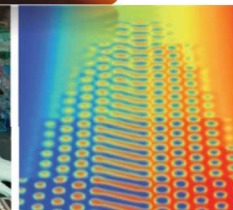
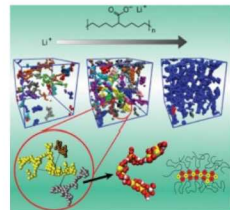
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